

### **Hydrogen interaction with point defects in the Si-SiO<sub>2</sub> structures and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn; Kämer, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A.** Solid state phenomena 2008 / p. 345-350

### **Impurity interaction with point defects in the Si-SiO<sub>2</sub> structures and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn; Kämer, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Medvid, A.** Materials science and engineering : B 2006 / p. 222-226 : ill <https://www.sciencedirect.com/science/article/pii/S0921510706004375>

### **Interaction between point defects in the Si-Si=2 system**

**Kropman, Daniel; Kämer, T.; Samoson, Ago; Heinmaa, I.; Mellikov, Enn** Nuclear instruments & methods in physics research. Section B 2002 / p. 78-82

### **Interaction between point defects in the Si-SiO<sub>2</sub> system during the process of its formation**

**Kropman, Daniel; Kämer, T.; Samoson, Ago; Heidmaa, I.; Ugaste, Ülo; Mellikov, Enn** Defect and Diffusion Forum 2001 / p. 1737-1744

### **Interaction between point defects, extended defects and impurities in the Si-SiO<sub>2</sub> system during the process of its formation**

**Kropman, Daniel; Kämer, T.; Abru, Uno; Ugaste, Ülo; Mellikov, Enn** Thin solid films 2004 / 1/2, p. 53-57 : ill

### **Interaction between point defects, extended defects and impurities in the Si-SiO<sub>2</sub> system during the process of its formation**

**Kropman, Daniel; Kämer, T.; Abru, Uno; Ugaste, Ülo; Mellikov, Enn; Kauk, Marit** Materials science and engineering : B 2004 / p. 295-298 : ill

### **Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn; Kämer, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej** Solid state phenomena 2011 / p. 263-266

### **Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Kämer, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos** Physica status solidi (c) 2011 / p. 694-696 : ill

### **Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Kämer, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, C. A.** The 9th International Conference on Global Research and Education : August 9-12, 2010, Riga : digest 2010 / p. 231-233  
<https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>

### **Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the properties of the interface**

**Kropman, Daniel; Mellikov, Enn; Lott, Kalju; Kämer, T.; Heinmaa, I.** Gettering and defect engineering in semiconductor technology XIII : CADEST 2009 : proceedings of the XIIIth International Autumn Meeting, Döllnsee-Schorfheide, north of Berlin, Germany, September 26 - October 02, 2009 2010 / p. 145-148 : ill

### **Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the properties of the interface**

**Kropman, Daniel; Mellikov, Enn; Lott, Kalju; Kämer, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.; Skroupa, W.; Prucnal, S.; Zvyagin, S.; Cizmar, E.; Ozerov, M.; Wosnitsa, J.** Solid state phenomena 2010 / p. 145-148 : ill  
<https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>

### **Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the properties of the interface**

**Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Kämer, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.; Skroupa, W.; Prucnal, S.; Rebohle, L.; Zvyagin, S.; Cizmar, E.; Ozerov, M.; Wosnitsa, J.** Thin solid films 2010 / 9, p. 2374-2376  
<https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>

### **Interaktsioon punktdefektide ja lisandite vahel süsteemis Si-SiO<sub>2</sub> ja nende mõju piirpinna omadustele : [ettekande sisukokkuvõte]**

**Kropman, Daniel; Kämer, T.; Heinmaa, I.** Eesti Füüsika Seltsi aastaraamat 2008 2009 / lk. 119-120

### **Investigation of strain relaxation mechanism in Si-SiO<sub>2</sub> system during the process of its formation**

**Kropman, Daniel; Poll, V.; Kämer, T.; Ugaste, Ülo; Mellikov, Enn; Arbu, Uno; Paomets, V.** Physica status solidi (a) 2003 / 2, p. 297-301 <https://onlinelibrary.wiley.com/doi/abs/10.1002/pssa.200306611>

### **Low-K factor of SiO<sub>2</sub> layer on Si irradiated by YAG:Nd laser**

**Medvid, A.; Onufrijevs, Pavels; Mellikov, Enn; Kropman, Daniel; Muktepavela, F.; Bakradze, G.** Journal of non-crystalline solids 2007 / p. 703-707 : ill <https://www.sciencedirect.com/science/article/pii/S0022309306014116>

### **Point defects interaction with extended defects and impurities and its influence on the Si-SiO<sub>2</sub> system properties**

**Kropman, Daniel;** Arbu, Uno; Kämer, T.; Ugaste, Ülo; **Mellikov, Enn;** **Kauk, Marit;** Heinmaa, I.; **Samoson, Ago;** Medvid, A. Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill

**Point defects interaction with extended defects in the Si-SiO<sub>2</sub> system [Electronic resource]**

Kropman, Daniel; Kämer, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Proceedings IV-C-16 : Venice, 2004 2004 / p. SS1-TuP394 [CD-ROM]

**Strain relaxation mechanism in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Volobujeva, Olga;** Kämer, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Radiation Interaction with Materials and its use in Technologies : Kaunas, 24-27.09.2008 2008 / p. 204-207

**Strain relaxation mechanism in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Volobujeva, Olga;** Kämer, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Physica B : condensed matter 2009 / 23/24, p. 5153-5155 : ill

**Stress relaxation mechanism by strain in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn;** Kämer, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262

**Understanding and control of stress at Si-SiO<sub>2</sub> interface**

Kropman, Daniel; Seeman, Viktor; Medvids, Arturs; Onufrijevs, Pavels; Vitusevich, Svetlana; **Mikli, Valdek** Key engineering materials 2020 / p. 291-296 <https://doi.org/10.4028/www.scientific.net/KEM.850.291> [Journal metrics at Scopus](#) [Article at Scopus](#)

**Влияние неоднородностей в моно- и поликристаллическом Cds на фотоэлектрические и длинновременные неравновесные свойства**

**Kropman, Daniel; Lott, Kalju;** Šeinkman, M. Физика, химия и технические применения полупроводников A2B6 : тезисы докладов IV всесоюзного совещания (Одесса, 16-19 ноября 1976 г.) 1976 / с. 123 [https://www.ester.ee/record=b2969209\\*est](https://www.ester.ee/record=b2969209*est)

**Влияние облучения низкоэнергетическими электронами в растровом электронном микроскопе на параметры полупроводниковых приборов**

**Meiler, Boriss; Kropman, Daniel; Levtsenkova, Alla** Микроэлектроника 1987 / с. 165-169 : илл [https://www.ester.ee/record=b2147720\\*est](https://www.ester.ee/record=b2147720*est)

**Исследование температурного тушения фотопроводимости в пленках CdS**

**Kropman, Daniel** Полупроводниковые материалы. 1 1969 / с. 107-113 : илл [https://www.ester.ee/record=b1346474\\*est](https://www.ester.ee/record=b1346474*est) <https://digikogu.taltech.ee/et/Item/da24f532-932d-41c5-8925-a52dfa4b18c8/>

**Исследование термостимулированной провидимости и эффекта Холла в пленках CdS**

**Kropman, Daniel** Полупроводниковые материалы. 1 1969 / с. 97-105 : илл [https://www.ester.ee/record=b1346474\\*est](https://www.ester.ee/record=b1346474*est) <https://digikogu.taltech.ee/et/Item/da24f532-932d-41c5-8925-a52dfa4b18c8/>

**Исследование уровней прилипания в пленках сульфида кадмия**

**Kropman, Daniel** Сборник статей по химии и химической технологии. 19 1968 / с. 87-92 : илл [https://www.ester.ee/record=b2182213\\*est](https://www.ester.ee/record=b2182213*est) <https://digikogu.taltech.ee/et/Item/026f8881-5a73-4588-acba-0b1ffe988b0f>